Silicon (Si)

Specialist Data Sheet

Product Name Silicon (Si)

Transmission Range 1.2 ~ 15 μ m

Refractive Index 3.4223 @ 5 μ m

Reflection Loss 46.2% @ 5 µm (2 surfaces)

Absorption Coefficient 0.01 @ 3 µm

Reststrahlen Peak n/a

dN/dT 160×10^{-6} /°C dN/du $10.4 \mu m$ Density 2.33 g/cc

Melting Point 1420 $^{\circ}$ C (softening) Thermal Conductivity 163.3 W m⁻¹ K⁻¹ @ 273K

Thermal Expansion 4.15×10^{-6} /°C

Hardness Knoop 1150
Specific Heat Capacity 703 J Kg⁻¹ K⁻¹
Dialectric Constant 13 @ 10 GHz

Youngs Modulus (E) 131 GPa Shear Modulus (G) 79.9 GPa Bulk Modulus (K) 102 GPa

Elastic Coefficients C11=167; C12=65; C44=80 Apparent Elastic Limit 124.1 Mpa (18000 psi)

Poisson Ratio 0.266

Solubility Insoluble in Water

Molecular Weight 28.09

Class/Structure Cubic diamond, Fd3m

Notes:

Silicon is grown by Czochralski pulling techniques (CZ) and contains some oxygen which causes an absorption band at 9 microns. To avoid this, material can be prepared by a Float-Zone (FZ) process. Optical silicon is generally lightly doped (5 to 40 ohm cm) for best transmission above 10 microns. Silicon has a further pass band 30 to 100 microns which is effective only in very high resistivity uncompensated material. Doping is usually boron (p-type) and phosphorus (n-type).

Application:

Silicon is used as an optical window primarily in the 3 to 5 micron band and as a substrate for production of optical filters. Large blocks with polished faces are also employed as targets in neutron physics experiments

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μ m	No						
1.357	3.4975	1.970	3.4537	4.000	3.4257	7.000	3.4189
1.367	3.4962	2.153	3.4476	4.258	3.4245	7.500	3.4186
1.395	3.4929	2.325	3.4430	4.500	3.4236	8.000	3.4184
1.5295	3.4795	2.714	3.4358	5.000	3.4223	8.500	3.4182
1.660	3.4696	3.000	3.4320	5.500	3.4213	10.00	3.4179
1.709	3.4664	3.303	3.430	6.000	3.4202	10.50	3.4178
1.813	3.4608	3.500	3.4284	6.500	3.4195	11.04	3.4176

Transmission Range Graph:

